

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|---|-----------------------------------|------------------|
| 6 | 431 | ((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity) | USPAT | 2003/12/02 15:52 |
| 8 | 307 | ((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)) and (implant or implanting or implantation or dope or doped or doping or dopant) | USPAT | 2003/12/02 10:01 |
| 9 | 282 | ((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)) and (implant or implanting or implantation or dope or doped or doping or dopant)) and (etch or etching) and @ay<=2001 | USPAT | 2003/12/02 10:01 |
| 10 | 167 | ((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)) and (implant or implanting or implantation or dope or doped or doping or dopant)) and (etch or etching) and @ay<=2001) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (al or aluminum or Ga or gallium or boron or B!)) | USPAT | 2003/12/02 15:36 |
| 11 | 21 | ("3886569" "4806199" "4807016" "5275972" "5286344" "5300463" "5424570" "5468342" "5562801" "5626716" "5695658" "5759888" "5814563" "5817580" "5841195" "5843845" "5843847" "5855962" "5965035" "6051870" "6239017").PN. | USPAT | 2003/12/02 12:08 |
| 12 | 290 | 438/705.ccls. | USPAT | 2003/12/02 15:36 |
| 13 | 650 | 438/706.ccls. | USPAT | 2003/12/02 15:36 |
| 14 | 118 | 348/714.ccls. | USPAT | 2003/12/02 15:36 |
| 15 | 729 | 438/723.ccls. | USPAT | 2003/12/02 15:36 |
| 16 | 393 | 438/724.ccls. | USPAT | 2003/12/02 15:37 |
| 17 | 38 | ((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity) | US-PGPUB; EPO; JPO; DERWENT | 2003/12/02 15:53 |
| - | 1 | 4514251.pn. | USPAT | 2003/12/01 13:41 |
| - | 1044 | ((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant) | USPAT | 2003/12/01 15:26 |
| - | 835 | ((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching) | USPAT | 2003/12/01 14:47 |

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|---|------|---|-------|---------------------|
| - | 779 | (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) | USPAT | 2003/12/01 14:47 |
| - | 546 | (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)) and (selective or selectively or selectivity) | USPAT | 2003/12/01 13:46 |
| - | 208 | (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)) and ((selective or selectively or selectivity) with (nitride or SiN or "Si.sub.3 N.sub.4")) | USPAT | 2003/12/01 14:39 |
| - | 147 | ((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant) | USPAT | 2003/12/01 14:47 |
| - | 103 | ((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching) | USPAT | 2003/12/01 14:47 |
| - | 94 | (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) | USPAT | 2003/12/01 14:47 |
| - | 1391 | ((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) | USPAT | 2003/12/01 15:27 |
| - | 1090 | (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity)) and (implant or implanting or implantation or dope or doped or doping or dopant) | USPAT | 2003/12/01 15:26 |
| - | 405 | ((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant) | USPAT | 2003/12/01 16:40 |
| - | 398 | (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 | USPAT | 2003/12/01 15:27 |

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|---|-----|---|-------|---------------------|
| - | 386 | (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) | USPAT | 2003/12/01 15:27 |
| - | 368 | (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (etch or etching) | USPAT | 2003/12/01 15:27 |
| - | 237 | (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (etch or etching)) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (aluminum or al or boron or B! or Ga! or gallium))) | USPAT | 2003/12/01 15:29 |
| - | 195 | ((((((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (etch or etching)) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (aluminum or al or boron or B! or Ga! or gallium))) and @py<=2001 | USPAT | 2003/12/01 16:40 |

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|---|-----|---|-------|---------------------|
| - | 134 | <p> (((((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (etch or etching)) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (aluminum or al or boron or B! or Ga! or gallium))) and @py<=2001) and (((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2")) </p> | USPAT | 2003/12/02 09:59 |
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